



#### 12V P-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
	$11m\Omega @ V_{GS} = -4.5V$	-11A
-12V	$14m\Omega @ V_{GS} = -3.7V$	-9.7A
	$19m\Omega @ V_{GS} = -2.5V$	-8.3A
	$30m\Omega @ V_{GS} = -1.8V$	-6.6A

## **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

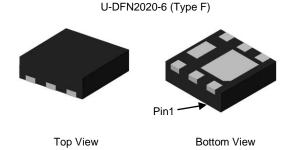
- Battery Management Application
- Power Management Functions
- DC-DC Converters

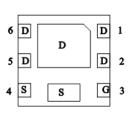
## **Features**

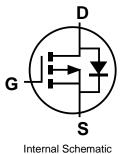
- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low On-Resistance
- · Fast Switching Speed
- 100% Unclamped Inductive Switching (Test in Production) Ensures More Reliability
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### **Mechanical Data**

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.007 grams (Approximate)







Pin Out Bottom View

**Ordering Information** (Note 5)

Part Number	Case	Packaging
DMP1009UFDFQ-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel
DMP1009UFDFQ-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



FZ = Product Type Marking Code YM = Date Code Marking Y = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

	Year	2017		2018	2019		2020	2021		2022	2023		2024
	Code	Е		F	G		Н			J	K		L
Γ	Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
	Code		_					-	_			N.I.	_



# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	$V_{DSS}$	-12	V		
Gate-Source Voltage			$V_{GSS}$	±8	V
	T <sub>A</sub> = +25°C		-11	۸	
Cantinuous Dunin Cumant V 4 5V (Note 7)	State	T <sub>A</sub> = +70°C	I <sub>D</sub>	-8.7	А
Continuous Drain Current V <sub>GS</sub> = -4.5V (Note 7)	t<5s	T <sub>A</sub> = +25°C	· I <sub>D</sub>	-15	۸
		T <sub>A</sub> = +70°C		-12	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	-70	Α		
Maximum Body Diode Continuous Current (Note 7)	Is	-2.5	Α		
Avalanche Current (Note 8) L = 0.1mH	I <sub>AS</sub>	-24	Α		
Avalanche Energy (Note 8) L = 0.1mH	E <sub>AS</sub>	31	mJ		

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit		
Total Power Dissipation (Note 6)	$T_A = +25$ °C	P <sub>D</sub>	0.8	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	152	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<5s	$R_{\theta JA}$	81	*C/VV	
Total Power Dissipation (Note 7)	$T_A = +25$ °C	$P_{D}$	2.0	W	
Thermal Desistance Junction to Ambient (Note 7)	Steady State	D.	63		
Thermal Resistance, Junction to Ambient (Note 7)	t<5s	$R_{\theta JA}$	34	°C/W	
Thermal Resistance, Junction to Case (Note 7)	Steady State	$R_{\theta JC}$	15		
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)		•			•		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-12	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		_	-100	nA	$V_{DS} = -9.6V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	1	±100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	$V_{GS(TH)}$	-0.3	_	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			8.3	11		$V_{GS} = -4.5V$ , $I_{D} = -5A$	
Static Drain-Source On-Resistance	Ь		9	14	mΩ	$V_{GS} = -3.7V, I_D = -5A$	
Static Dialif-Source Off-Resistance	R <sub>DS(ON)</sub>	_	12	19	11177	$V_{GS} = -2.5V, I_{D} = -4A$	
			16	30		$V_{GS} = -1.8V, I_{D} = -1A$	
Diode Forward Voltage	$V_{SD}$		-0.8	-1.2	V	$V_{GS} = 0V, I_{S} = -10A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C <sub>iss</sub>		1860			101/11/	
Output Capacitance	Coss	_	498	_	pF	$V_{DS} = -10V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	416	_		1 - 1.000112	
Gate Resistance	$R_g$	_	11	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Qg	_	26	_			
Total Gate Charge (V <sub>GS</sub> = -8V)	Qg	_	44	_	nC		
Gate-Source Charge	$Q_{gs}$	_	3.3	_	IIC	$V_{DS} = -6V, I_{D} = -10A$	
Gate-Drain Charge	$Q_{gd}$	_	8.1	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	7.0	_			
Turn-On Rise Time	t <sub>R</sub>	_	10.6	_		$V_{DS} = -6V, V_{GS} = -4.5V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	62.2	_	ns	$R_g = 1\Omega$ , $I_D = -8A$	
Turn-Off Fall Time	t <sub>F</sub>	_	61	_			
Reverse Recovery Time	t <sub>RR</sub>	_	34.4	_	ns	1 400 11/14 5000/	
Reverse Recovery Charge	$Q_{RR}$	_	28.1	_	nC	$I_F = -12A$ , di/dt = 500A/ $\mu$ s	

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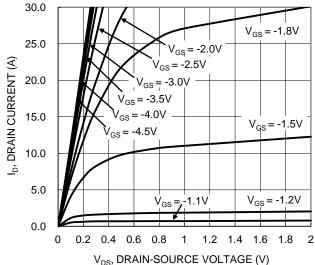
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. Notes:

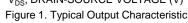
<sup>8.</sup>  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J$  = +25°C.

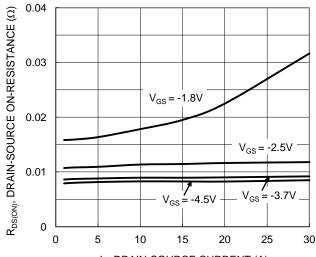
<sup>9.</sup> Short duration pulse test used to minimize self-heating effect.

<sup>10.</sup> Guaranteed by design. Not subject to product testing.









I<sub>D</sub>, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

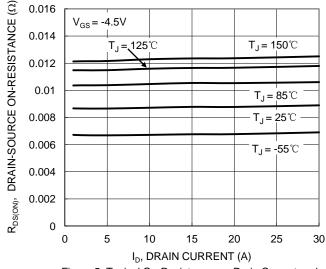


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

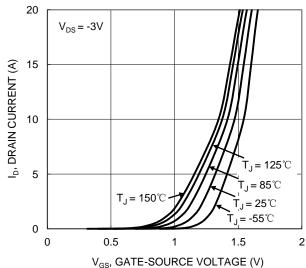


Figure 2. Typical Transfer Characteristic

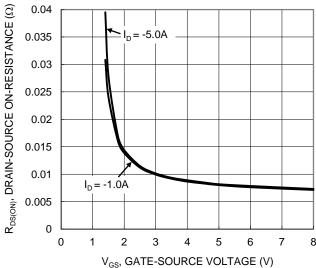


Figure 4. Typical Transfer Characteristic

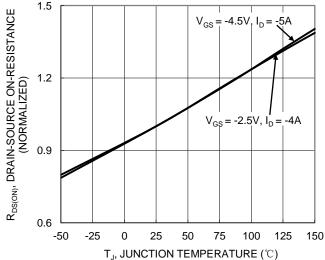


Figure 6. On-Resistance Variation with Temperature





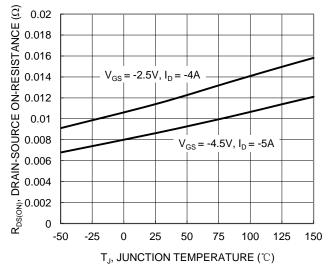
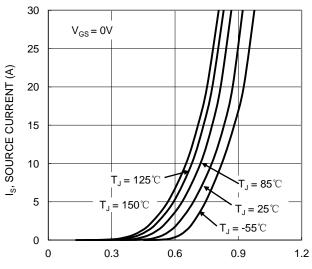


Figure 7. On-Resistance Variation with Temperature



V<sub>SD</sub>, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

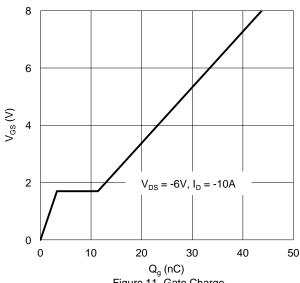


Figure 11. Gate Charge

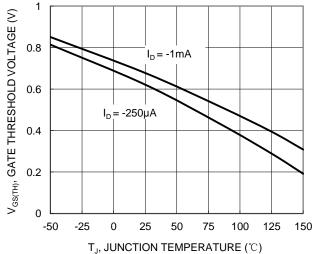


Figure 8. Gate Threshold Variation vs. Junciton Temperature

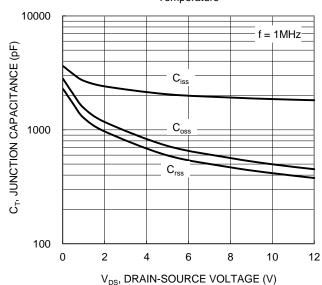
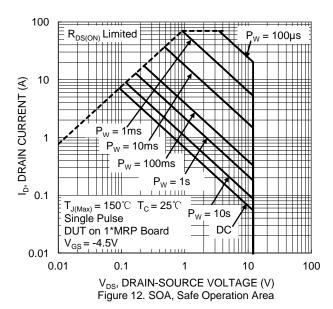


Figure 10. Typical Junction Capacitance





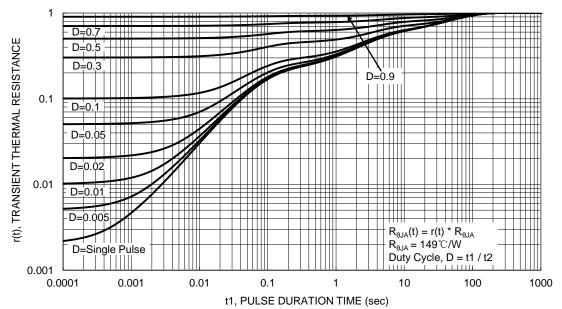


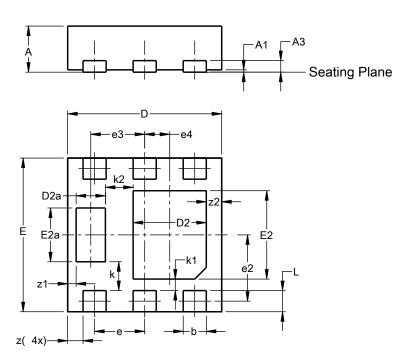
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN2020-6 (Type F)

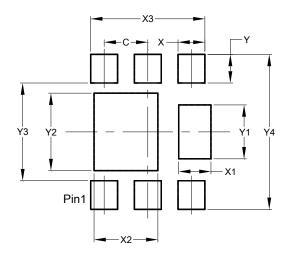


U-DFN2020-6									
	(Type F)								
Dim	Min Max Typ								
Α	0.57	0.63	0.60						
A1	0.00	0.00 0.05 0.03							
A3	-	-	0.15						
b	0.25	0.35	0.30						
D	1.95	2.05	2.00						
D2	0.85	1.05	0.95						
D2a	0.33	0.43	0.38						
E	1.95	2.05	2.00						
E2	1.05	1.25	1.15						
E2a	0.65	0.75	0.70						
е	0.65 BSC								
e2	0.863 BSC								
е3		0.70 BS	С						
e4	(	).325 BS	SC						
k		0.37 BS	С						
k1	0.15 BSC								
k2		0.36 BS	С						
L	0.225	0.325	0.275						
Z		0.20 BS	С						
<b>z</b> 1	(	).110 BS	SC						
z2	0.20 BSC								
All Dimensions in mm									

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### U-DFN2020-6 (Type F)



Dimensions	Value (in mm)		
С	0.650		
Х	0.400		
X1	0.480		
X2	0.950		
Х3	1.700		
Y	0.425		
Y1	0.800		
Y2	1.150		
Y3	1.450		
Y4	2.300		



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